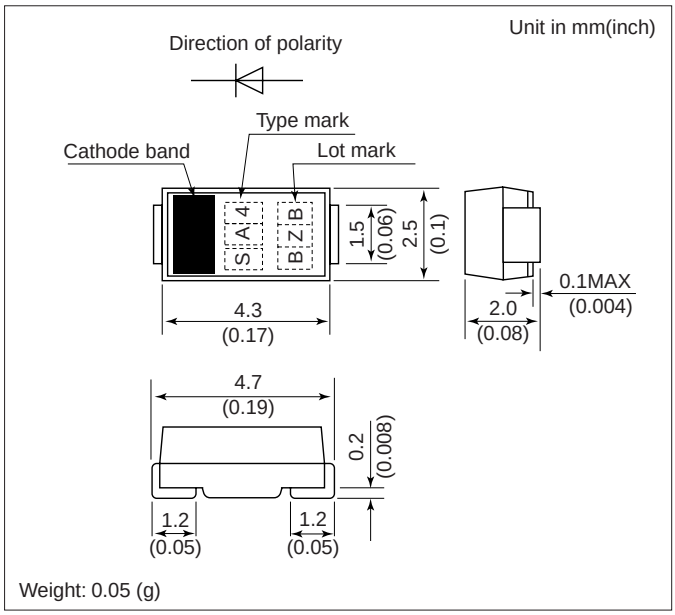
DSM1MA

FEATURES

- For general purpose
- High heat-resistant due to glass passivation.

OUTLINE DRAWING



Weight: 0.05 (g)

ABSOLUTE MAXIMUM RATINGS

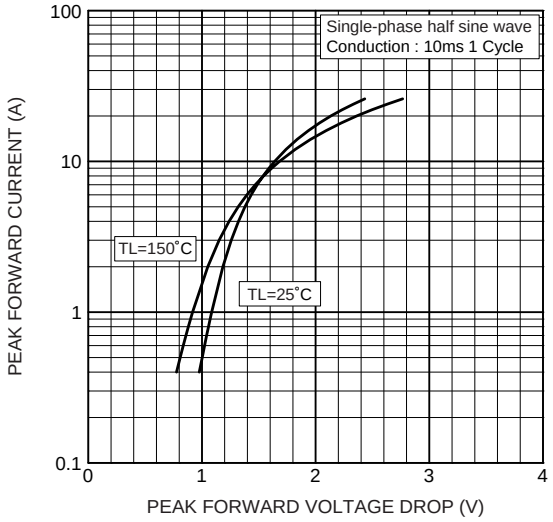
Items	Type		DSM1MA1	DSM1MA2	DSM1MA4
Repetitive Peak Reverse Voltage	V_{RRM}	V	100	200	400
Average Forward Current	$I_{F(AV)}$	A	1.0 (Single-phase half sine wave 180° conduction, TL = 127°C)		
Surge(Non-Repetitive) Forward Current	I_{FSM}	A	25(Without PIV, 10ms conduction, Tj = 40°C start)		
I^2t Limit Value	I^2t	A^2s	2.5(Time = 2 ~ 10ms, I = RMS value)		
Operating Junction Temperature	T_j	°C	-40 ~ +150		
Storage Temperature	T_{stg}	°C	-40 ~ +150		

CHARACTERISTICS(T_L=25°C)

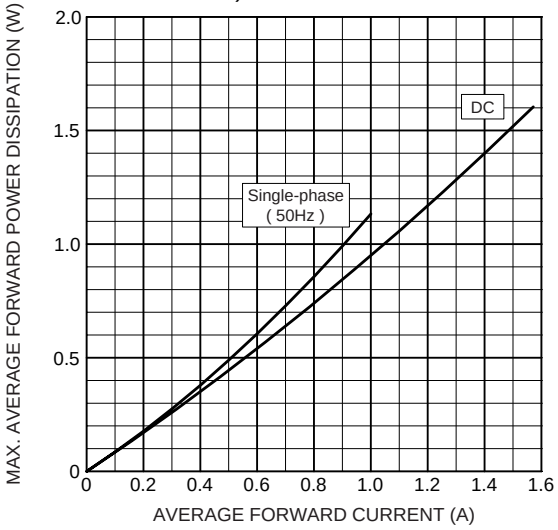
Items	Symbols	Units	Min.	Typ.	Max.	Test Conditions	
Peak Reverse Current	I_{RRM}	μA	–	–	20	DSM1MA1,2	Rated V_{RRM}
					10	DSM1MA4	
Peak Forward Voltage	V_{FM}	V	–	–	1.1	I_{FM}=1.0Ap, Single-phase half sine wave 1 cycle	
Steady State Thermal Impedance	$R_{th(j-a)}$	°C/W	–	–	120	On glass-epoxi substrate (□ 50mm)	
	$R_{th(j-l)}$				20	Soldering land (□ 6mm)	

DSM1MA

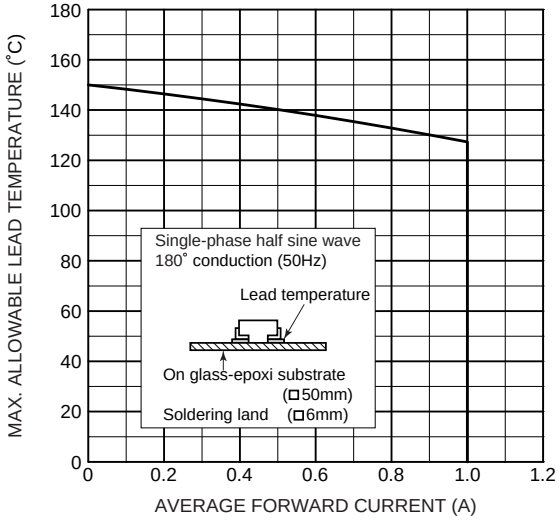
Forward characteristics



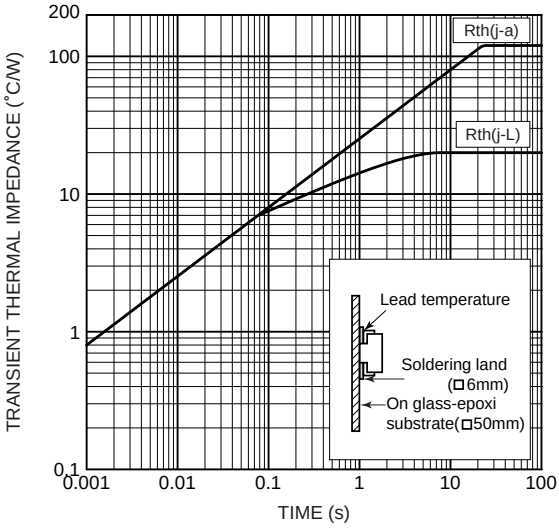
Max. average forward power dissipation
(Resistive or inductive load)



Max. allowable lead temperature
(Resistive or inductive load)



Transient thermal impedance



HITACHI POWER SEMICONDUCTORS

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